

4.1
Docket No. 215686US99CIP

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Fred RICHARD, et al.

SERIAL NO: 09/985,757

GAU: 2811

FILED: November 6, 2001

EXAMINER: HU, S.

FOR: MICROCAVITY SEMICONDUCTOR LASER COUPLED TO A WAVEGUIDE



INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were submitted in application Serial No. 09/908,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- ☒ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

Richard L. Treanor

Registration No. 36,379

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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 215686US99CIP		SERIAL NO. 09/985,757	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Fred RICHARD, et al.			
				FILING DATE November 6, 2001		GROUP 2811	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shasstry			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Mantl et al.			
	BE	5,741,724	04/21/98	Ramdanl et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thomton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijali et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunel et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganei et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			

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EA		4,484,332	11/20/84	Hawrylo			
EB		4,815,084	03/21/89	Scifres et al.			
EC		4,876,219	10/24/89	Eshita et al.			
ED		4,963,508	10/16/90	Umeno et al.			
EE		5,060,031	10/22/91	Abrokwah, et al.			
EF		5,063,166	11/05/91	Mooney et al.			
EG		5,116,461	05/26/92	Lebby et al.			
EH		5,127,067	06/30/92	Delcoco et al.			
EI		5,144,409	09/01/92	Ma			
EJ		5,293,050	03/08/94	Chapple-Sokol et al			
EK		5,356,831	10/18/94	Calviello et al.			
EL		5,391,515	02/21/95	Kao et al.			
EM		5,442,191	08/15/95	Ma			
EN		5,444,016	08/22/95	Abrokwah, et al.			
EO		5,480,829	01/02/96	Abrokwah, et al.			
EP		5,528,414	06/18/96	Oakley			
EQ		5,614,739	03/25/97	Abrokwah et al.			
ER		5,729,394	03/17/98	Sevier et al.			
ES		5,731,220	03/24/98	Tsu et al.			
ET		5,764,676	06/09/98	Paoli et al.			
EU		5,777,762	07/07/98	Yamamoto			
EV		5,778,018	07/07/98	Yoshikawa et al.			
EW		5,778,116	07/07/98	Tomich			
EX		5,801,105	09/01/98	Yano et al.			
EY		5,828,080	10/27/98	Yano et al.			
EZ		5,858,814	01/12/99	Goossen et al.			
FA		5,861,966	01/19/99	Ortel			
FB		5,883,996	03/16/99	Knapp et al.			
FC		5,995,359	11/30/99	Klee et al.			
FD		6,058,131	05/02/00	Pan			
FE		6,137,603	10/24/00	Henmi			
FF		6,146,906	11/14/00	Inoue et al.			
FG		6,173,474	01/16/01	Conrad			
FH		6,180,252	01/30/01	Farrell et al.			
FI		4,242,595	12/30/0	Lehovec			
FJ		4,398,342	08/16/83	Pitt et al.			
FK		4,424,589	01/03/84	Thomas et al.			
FL		4,876,208	10/24/89	Gustafson et al.			
FM		4,482,422	11/84	McGinn et al.			
FN		4,667,088	05/19/87	Kramer			
FO		4,772,929	09/20/88	Manchester et al.			
FP		4,841,775	06/27/89	Ikedo et al.			

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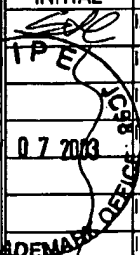
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

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	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
	IU	5,844,260	12/01/98	Ohori			
	IV	5,846,846	12/08/98	Suh et al.			
	IW	5,863,326	01/26/99	Nause et al.			
	IX	5,872,493	02/16/99	Ella			
	IY	5,879,956	03/99	Seon et al.			
	IZ	5,880,452	03/09/99	Plesko			
	JA	5,883,564	03/16/99	Parlin			
	JB	5,907,792	05/25/99	Droopad et al.			
	JC	5,937,274	08/10/99	Kondow et al.			
	JD	5,948,161	09/07/99	Kizuki			
JE	5,959,879	09/28/99	Koo				
JF	5,966,323	10/99	Chen et al.				
JG	5,987,011	11/16/99	Toh				
JH	6,022,140	02/08/00	Fraden et al.				
JI	6,022,410	02/08/00	Yu et al.				
JJ	6,023,082	02/08/00	McKee et al.				
JK	6,028,853	02/22/00	Haartsen				
JL	6,049,702	04/11/00	Tham et al.				
JM	6,078,717	06/20/00	Nashimoto et al.				
JN	6,088,216	07/00	Laibowitz et al.				
JO	6,090,659	07/00	Laibowitz et al.				
JP	6,107,721	08/22/00	Lakin				

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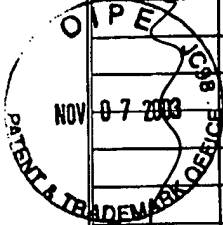
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U.S. PATENT DOCUMENTS

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MA		5,553,089	09/03/96	Seki et al.			
MB		5,528,057	06/18/96	Yanagase et al.			
MC		6,229,159	05/08/01	Suzuki			
MD		4,748,485	05/31/88	Vasudev			
ME		4,984,043	01/08/91	Vinal			
MF		5,754,319	05/19/98	Van De Voorde et al.			
MG		6,108,125	08/22/00	Yano			
MH		5,073,981	12/17/91	Giles et al.			
MI		5,140,651	08/18/92	Soref et al.			
MJ		5,610,744	03/11/97	Ho et al.			
MK		6,362,017	03/26/02	Manabe et al.			
ML		6,242,686	06/05/01	Kishimoto et al.			
MM		5,689,123	11/18/97	Major et al.			
MN		5,670,800	09/23/97	Nakao et al.			
MO		5,067,809	11/26/91	Tsubota			
MP		5,596,205	01/21/97	Reedy et al.			
MQ		6,175,555	01/16/01	Hoole			
MR		5,357,122	10/18/94	Okubora et al.			
MS		4,084,130	04/11/78	Holton			
MT		6,093,302	07/25/00	Montgomery			
MU		6,372,813	04/16/02	Johnson et al.			
MV		5,608,046	03/04/97	Cook et al.			
MW		5,955,591	09/21/99	Imbach et al.			
MX		6,022,963	02/08/00	McGall et al.			
MY		6,083,697	07/04/00	Beecher et al.			
MZ		5,063,081	11/05/91	Cozzette et al.			
NA		5,479,317	12/26/95	Ramesh			
NB		5,306,649	04/26/94	Hebert			
NC		5,962,069	10/05/99	Schindler et al.			
ND		5,541,422	07/30/96	Wolf et al.			
NE		5,873,977	02/23/99	Desu et al.			
NF		5,538,941	07/23/96	Findikoglu et al.			
NG		6,046,464	04/04/00	Schetzina			
NH		6,235,145	05/22/01	Li et al.			
NI		5,610,744	03/11/97	Ho et al.			
NJ		5,280,013	01/18/94	Newman et al.			
NK		6,348,373 B1	02/19/02	Ma et al.			
NL		6,339,664 B1	01/15/02	Farjady et al.			
NM		4,439,014.	03/27/84	Stacy et al.			
NN		4,889,402	12/26/89	Reinhart			
NO		5,963,291	10/05/99	Wu et al.			
NP		6,011,641	01/04/00	Shin et al.			
NQ		6,340,788 B1	01/22/02	King et al.			



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OP	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
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	PC	6,275,122 B1	08/14/01	Speidell et al.			
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QC		5,834,362	11/10/98	Miyagaki et al.			
QD		6,248,621 B1	06/19/01	Wilk et al.			
QE		5,266,355	11/30/93	Wernberg et al.			
QF		6,277,436 B1	08/21/01	Stauf et al.			
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QI		5,420,102	05/30/95	Harshavardhan et al.			
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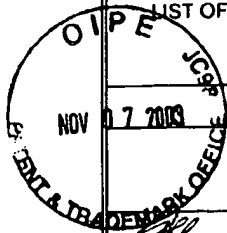
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AAC	0 455 526	06/11/91	EP	X	
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AAE	0 607 435	07/27/94	EP	X	
AAF	1 001 468	05/17/00	EP	X	
AAG	0 514 018	11/19/92	EP	X	
AAH	0 999 600	05/10/00	EP	X	
AAI	1 319 311	06/04/70	Great Britain	X	
AAJ	5-291299	11/05/93	Japan w/English Abstract	X	
AAK	11-238683	08/31/99	Japan	X	
AAL	11-260835	09/24/99	Japan w/English Abstract	X	
AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X	
AAN	5-48072	02/26/93	Japan w/English Abstract	X	
AAO	52-88354	07/23/77	Japan w/English Abstract	X	
AAP	54-134554	10/19/79	Japan w/English Abstract	X	
AAQ	55-87424	07/02/80	Japan w/English Abstract	X	
AAR	61-108187	05/26/86	Japan w/English Abstract	X	
AAS	6-232126	08/19/94	Japan	X	
AAT	6-291299	10/18/94	Japan w/English Abstract	X	
AAU	63-34994	02/15/88	Japan w/English Abstract	X	
AAV	63-131104	06/03/88	Japan w/English Abstract	X	
AAW	63-198365	08/17/88	Japan w/English Abstract	X	
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ABE	WO 00/48239	08/17/00	WIPO		
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ABG	GB 2 335 792	09/29/99	Great Britain		
ABH	1 109 212	06/20/01	Europe		
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ABJ	60-212018	10/24/85	Japan w/English Abstract		
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ABL	WO 92/10875	06/25/92	WIPO		
ABM	0 682 266	11/15/95	Europe		
ABN	3-41783	02/91	Japan (English Abstract only)		
ABO	0 581 239	02/02/94	Europe		
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	BAB	2000-068466	03/00	Japan (Abstract)			
	BAC	64-50575	02/27/89	Japan			
	BAD	WO 98/05807	01/12/98	WIPO			
	BAE	WO 94/03908	02/17/94	WIPO			
	BAF	WO 01/33585	05/10/01	WIPO			
	BAG	1-102435	04/20/89	Japan w/English Abstract			
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	BAO	58-213412	12/12/83	Japan w/English Abstract			
	BAP	0 964 259	12/15/99	Europe			
	BAQ	0 875 922	11/04/98	Europe			
	BAR	61-63015	04/01/86	Japan w/English Abstract			
	BAS	11340542	12/10/99	Japan (English Abstract)			
	BAT	WO 01/37330	05/25/01	WIPO			
	BAU	0 331 467	09/06/89	Europe			
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	BAX	0 964 453	12/15/99	Europe			
	BAY	5-152529	06/18/93	Japan w/English Abstract			
	BAZ	9-67193	03/11/97	Japan w/English Abstract			
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	BBH	WO 02/33385 A2	04/25/02	WIPO			
	BBI	WO 01/59814 A2	08/16/01	WIPO			
	BBJ	WO 02/09160 A2	01/31/02	WIPO			
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CAF	61-36981	02/21/86	Japan w/English Abstract		
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CAH	2002-9366	01/11/02	Japan w/English Abstract		
CAI	EP 0 881 669	12/02/98	Europe		
CAJ	WO 02/03480	01/10/02	WIPO		
CAK	WO 02/50879	06/27/02	WIPO		
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CAP	EP 0 993 027	04/12/00	Europe		
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CAR	WO 98/20606	05/14/98	WIPO		
CAS	EP 1 043 765	10/11/00	Europe		
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CAU	EP 1 085 319	03/21/01	Europe		
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Examiner

Shourmang

Date Considered

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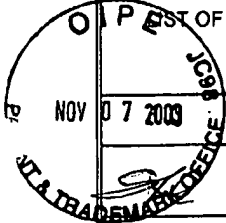
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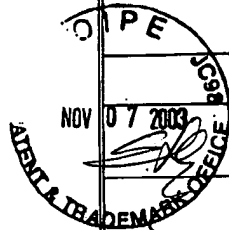
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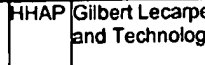
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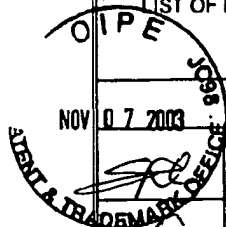
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JJAK	C. Donn et al.; "A 16-Element, K-Band Monolithic Active Receive Phased Array Antenna"; Antennas and Propagation Society International Symposium, 1988; pp.188-191, Vol. 1; 6-10 June 1988
JJAL	Don W. Shaw; "Epitaxial GaAs on Si: Progress and Potential Applications"; Mat. Res. Soc. Symp. Proc.; pp.15-30; 1987
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JJAN	P.J. Borrelli et al.; "Compositional and Structural Properties of Sputtered PLZT Thin Films"; Ferroelectric Thin Films II Symposium; Dec. 2-4, 1991 (Abstract)
JJAO	Ranu Nayak et al; "Enhanced acousto-optic diffraction efficiency in a symmetric SrTiO ₃ /BaTiO ₃ /SrTiO ₃ thin-film heterostructure"; 1 November 2000; Vol. 39, No. 31; Applied Optics; pp. 5847-5853
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KKAB	Katherine Derbyshire; "Prospects Bright for Optoelectronics Volume, Cost Drive Manufacturing for Optical Applications"; Semiconductor Magazine; Vol. 3, No. 3; March 2002		
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KKAD	S.A. Chambers et al; "Band Discontinuities at Epitaxial SrTiO ₃ /Si(001) Heterojunctions"; Applied Physics Letters; Vol. 77, No. 11; September 11, 2000; pp. 1662-1664		
KKAE	H. Wang et al.; "GaAs/GaAlAs Power HBTs for Mobile Communications"; Microwave Symposium Digest; 1993 IEEE; Vol. 2; pp. 549-552		
KKAF	Y. Ota et al.; "Application of Heterojunction FET to Power Amplifier for Cellular Telephone"; Electronics Letters; 26th May 1994; Vol. 30, No. 11; pp. 906-907		
KKAG	Keiichi Sakuno et al; "A 3.5W HBT MMIC Power Amplifier Module for Mobile Communications"; IEEE 1994; Microwave and Millimeter-Wave Monolithic Circuits Symposium; pp. 63-66		
KKAH	Mitsubishi Semiconductors Press Release (GaAs FET's) November 8, 1999 pp.1-2		
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KKAO			
KKAP			
KKAQ			
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<i>EX</i>	UT	5,528,209	06/18/96	Macdonald et al.			
	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
	UZ	5,559,368	09/24/96	Hu et al.			
	VA	6,392,253 B1	05/21/02	Saxena			
	VB	5,585,288	12/17/96	Davis et al.			
	VC	5,268,327	12/07/93	Vernon			
	VD	6,198,119 B1	03/06/01	Nabatame et al.			
	VE	6,113,225	09/05/00	Miyata et al.			
	VF	5,262,659	11/16/93	Grudkowski et al.			
	VG	6,239,012 B1	05/29/01	Kinsman			
	VH	6,297,598	10/02/01	Wang et al.			
	VI	2002/140012	10/03/02	Droopad			
	VJ	4,866,489	09/12/89	Yokogawa et al.			
	VK	6,080,378	06/27/00	Yokota et al.			
	VL	5,508,554	04/16/96	Takatani et al.			
	VM	6,477,285 B1	11/05/02	Shanley			
	VN	4,695,120	09/22/87	Holder			
	VO	5,882,948	03/16/99	Jewell			
	VP	5,574,589	11/12/96	Feuer et al.			
	VQ	5,510,665	04/23/96	Conley			
	VR	4,804,866	02/14/89	Akiyama			
	VS	5,057,694	10/15/91	Idaka et al.			
	VT	5,635,453	06/03/97	Pique et al.			
	VU	5,719,417	02/17/98	Roeder et al.			
	VV	5,998,819	12/07/99	Yokoyama et al.			

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	VX	5,148,504	09/15/92	Levi et al.			
	VY	2002/0195610 A1	12/26/02	Klosowiak			
	VZ	5,477,363	12/19/95	Matsuda			
	WA	5,905,571	05/18/99	Butler et al.			
	WB	5,570,226	10/29/96	Ota			
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	WD	2001/0020278 A1	09/06/01	Saito			
	WE	6,496,469 B1	12/17/02	Uchizaki			
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	WG	2001/0036142 A1	11/01/01	Kadowaki et al.			
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SR	WY	5,878,175	03/02/99	Sonoda et al.			
	WZ	4,801,184	01/31/89	Revelli			
	XA	5,140,387	08/18/92	Okazaki et al.			
	XB	5,410,622	04/25/95	Okada et al.			
	XC	6,064,783	05/16/00	Congdon et al.			
	XD	5,772,758	06/30/98	Collins et al.			
	XE	5,666,376	09/09/97	Cheng			
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	XK	6,504,189	01/07/03	Matsuda et al.			
	XL	5,987,196	11/16/99	Noble			
	XM						
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CBC	EP 1 035 759	09/13/00	Europe		
CBD	EP 0 860 913	08/26/95	EUROPE		
CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT		
CBF	5-243525	09/31/93	JAPAN W/ENGLISH ABSTRACT		
CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT		
CBH	EP 1 089 338	04/04/01	EUROPE		
CBI	01 294594	11/28/99	JAPAN (ABSTRACT)		
CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)		
CBK	03-149882	11/07/89	JAPAN		
CBL	0 614 256	09/07/94	EUROPE		
CBM	1 054 442	11/22/00	EUROPE		
CBN	0 852 416	07/08/98	EUROPE		
CBO	W0 02/08806	01/31/02	WIPO		
CBP	W0 01/59837	08/16/01	WIPO		
CBQ	62-245205	10/26/87	JAPAN W/ENGLISH ABSTRACT		
CBR	0 600 658	06/08/94	EUROPE		
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CBT	2000-349278	12/15/00	JAPAN (ENGLISH ABSTRACT)		
CBU	01-196809	08/08/89	JAPAN (ENGLISH ABSTRACT)		
CBV	0 619 283	10/12/94	EUROPE		
CBW	0 661 561	07/05/95	EUROPE		
CBX	0 331 338	09/06/89	EUROPE		
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XQ		6,415,140 B1	07/02/02	BENJAMIN ET AL			
XR		5,760,740	06/02/98	BLODGETT			
XS		5,238,877	08/24/93	RUSSELL			
XT		4,876,218	10/24/89	PESSA ET AL			
XU		6,232,242 B1	05/15/01	HATA ET AL			
XV		4,378,259	03/29/83	HASEGAWA ET AL			
XW		6,278,541 B1	08/21/01	BAKER			
XY		4,298,247	11/03/81	MICHELET ET AL			
XZ		4,174,504	11/13/79	CHENAUSSKY ET AL			
YA		3,758,199	09/11/73	THAXTER			
YB		6,362,558 B1	03/26/02	FUKUI			
YC		6,140,746	10/31/00	MIYASHITA ET AL			
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YE		6,419,849 B1	07/16/02	QIU ET AL			
YF		2002/0179000 A1	12/05/02	LEE ET AL			
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YN		5,523,602	06/04/96	HORIUCHI ET AL			
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	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
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	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
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	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
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	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
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ZT	5,166,761	11/24/92	OLSON ET AL				
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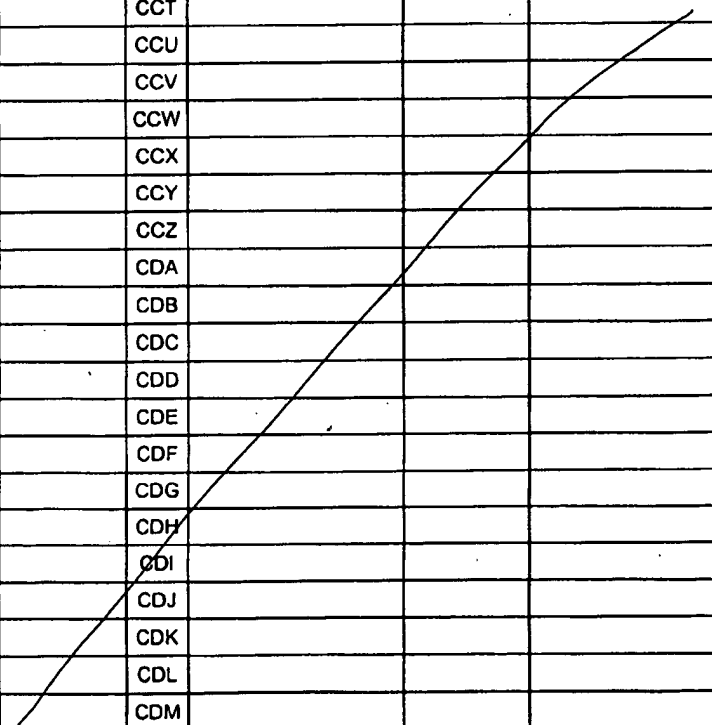
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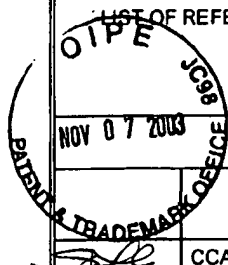
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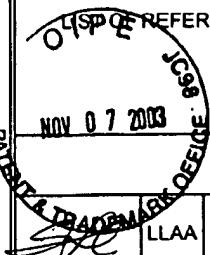
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	CCB	2 152 315	07/31/85	GREAT BRITAIN		
	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT		
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)		
	CCE	WO 03/012874	02/13/03	WIPO		
	CCF	1 043 427	10/11/00	EUROPE		
	CCG	1 069 605	01/17/01	EUROPE		
	CCH	WO 02/099885	12/12/02	WIPO		
	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT		
	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)		
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	CCM	0 494 514	07/15/92	EUROPE		
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	CCP	59-073498	04/25/84	JAPAN (ENGLISH ABSTRACT)		
	CCQ	60-161635	08/23/85	JAPAN W/ENGLISH ABSTRACT		
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	CCS	0 392 714	10/17/90	EUROPE		
	CCT					
	CCU					
	CCV					
	CCW					
	CCX					
	CCY					
	CCZ					
	CDA					
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LSP OF REFERENCES CITED BY APPLICANT 				APPLICANT Fred RICHARD, et al.			
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Examiner <i>Shouxiang He</i>						Date Considered <i>1/28/04</i>	
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							